

FIG. 1

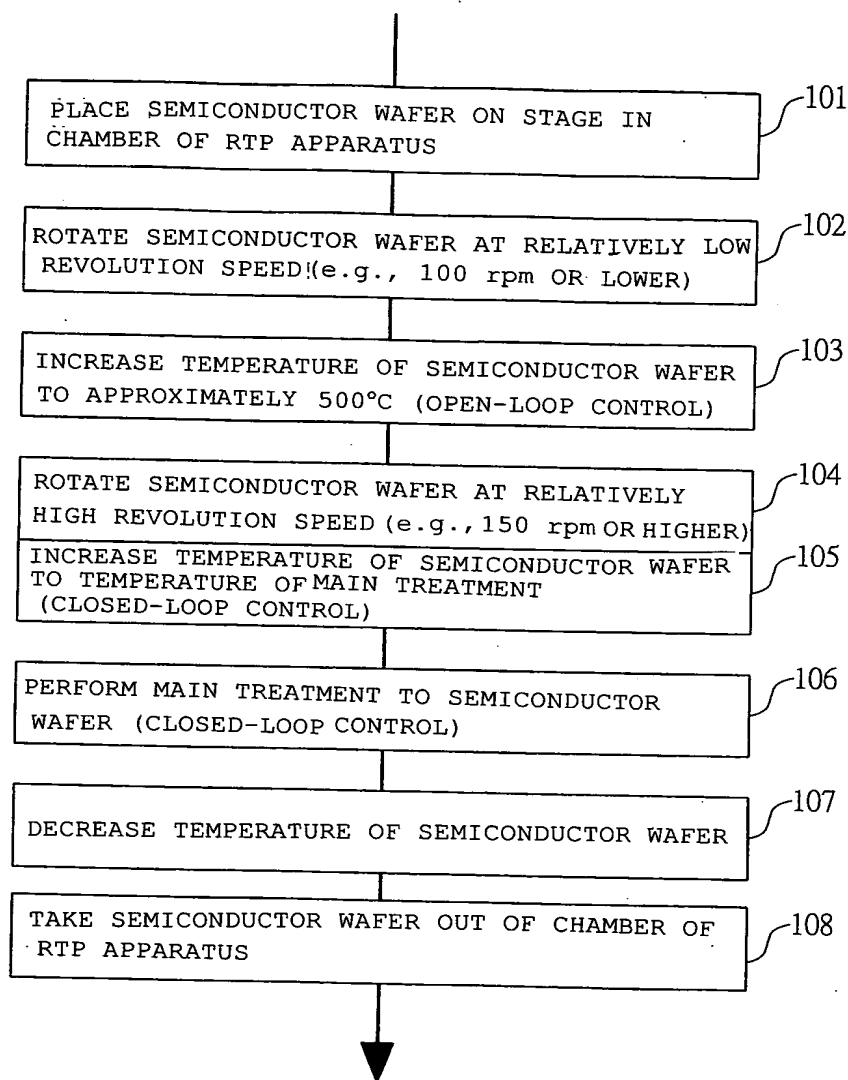


FIG. 2

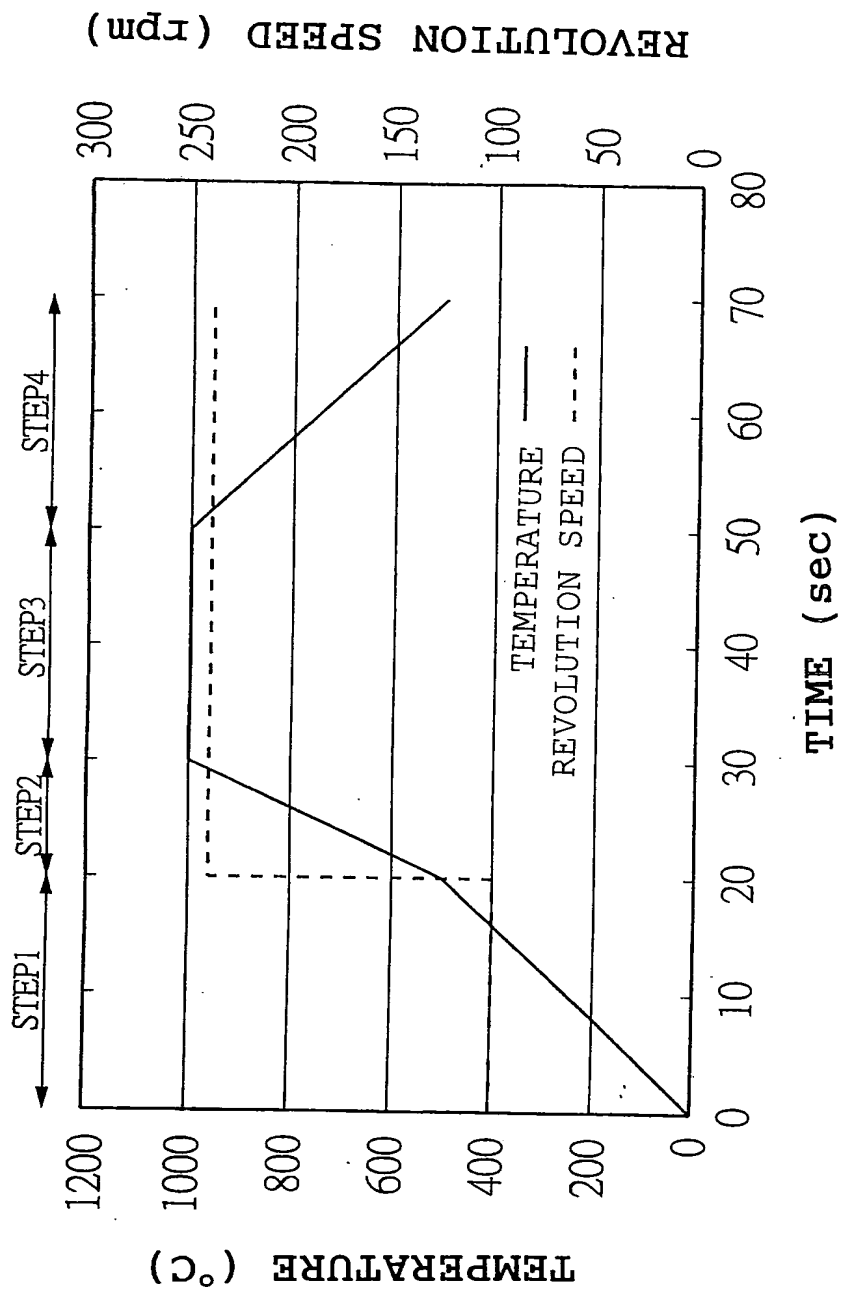


FIG. 3

FIG. 3A

START ROTATION OF SEMICONDUCTOR
WAFER

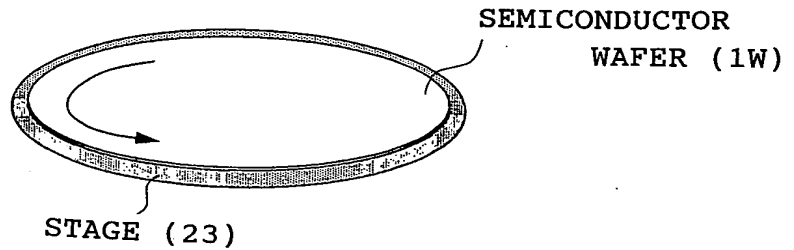


FIG. 3B

TEMPERATURE RISING PROCESS AT 500°C OR LOWER
(NONUNIFORM IN-PLANE TEMPERATURE OF SEMICONDUCTOR WAFER)

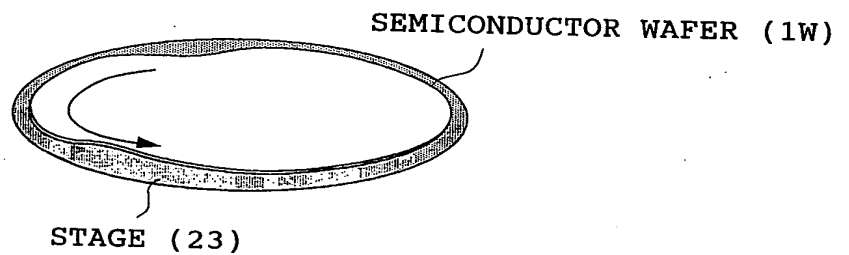


FIG. 3C

TEMPERATURE RISING PROCESS ABOVE 500°C AND MAIN
TREATMENT PROCESS (UNIFORM IN-PLANE TEMPERATURE OF
SEMICONDUCTOR WAFER)

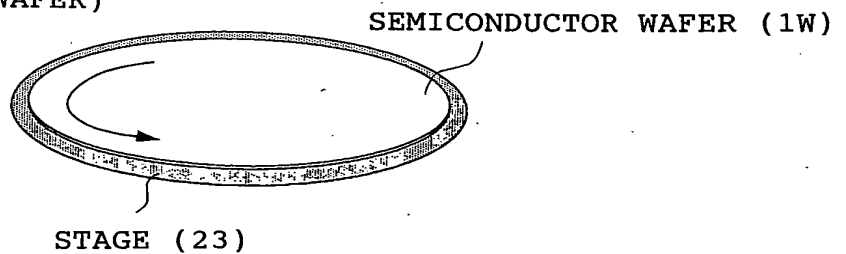


FIG. 4

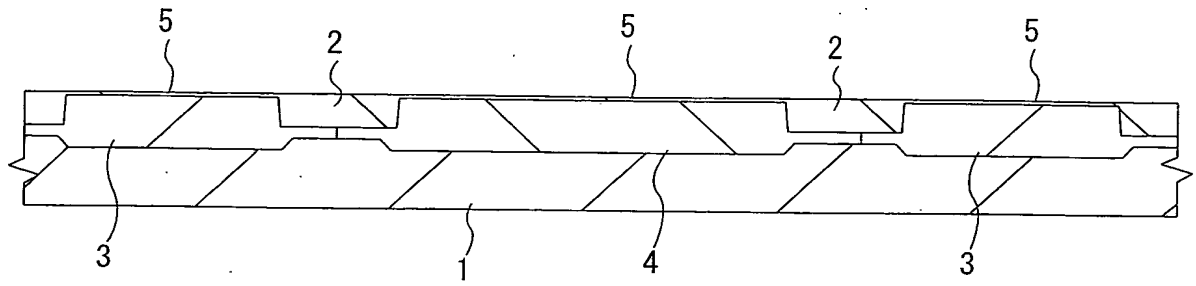


FIG. 5

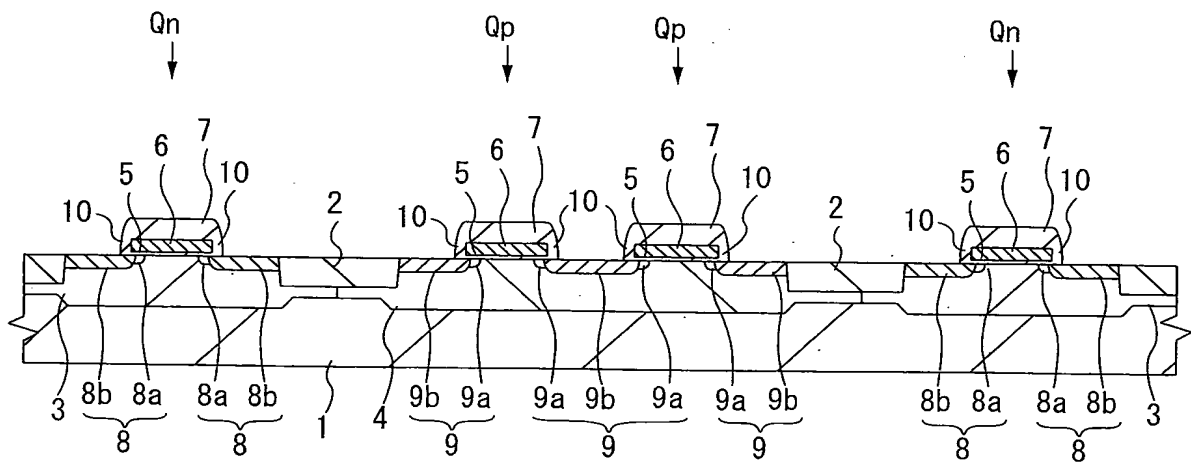


FIG. 6

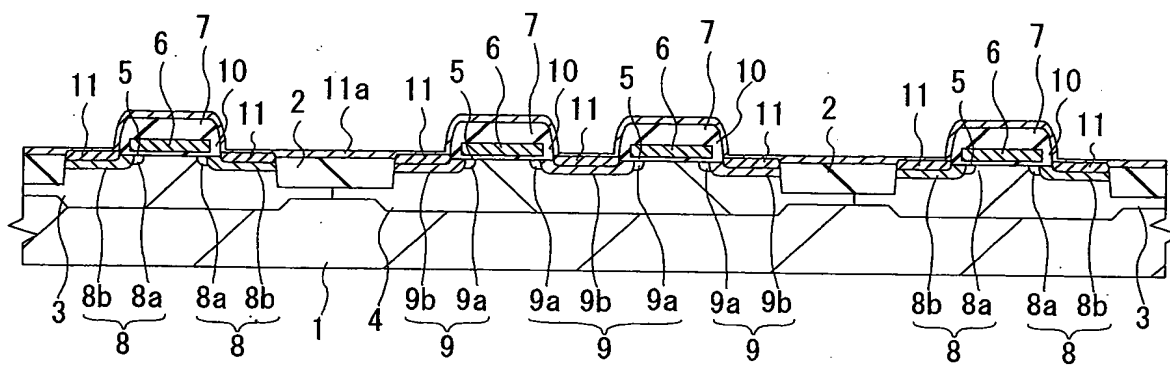


FIG. 7

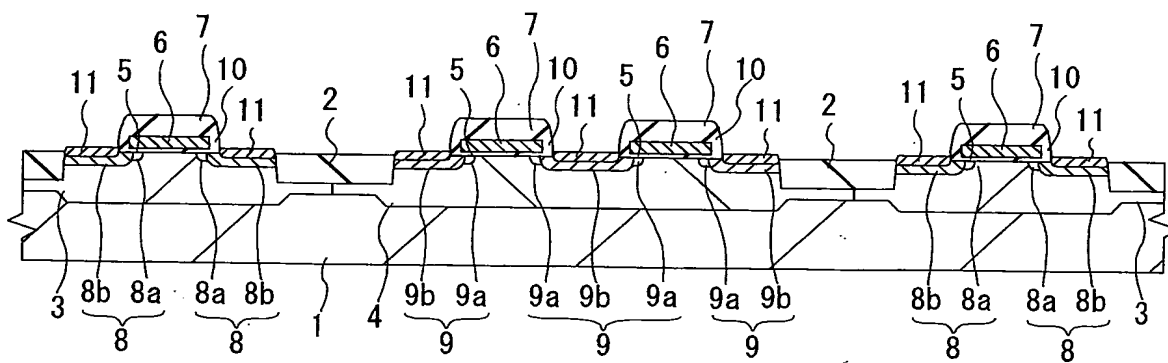


FIG. 8

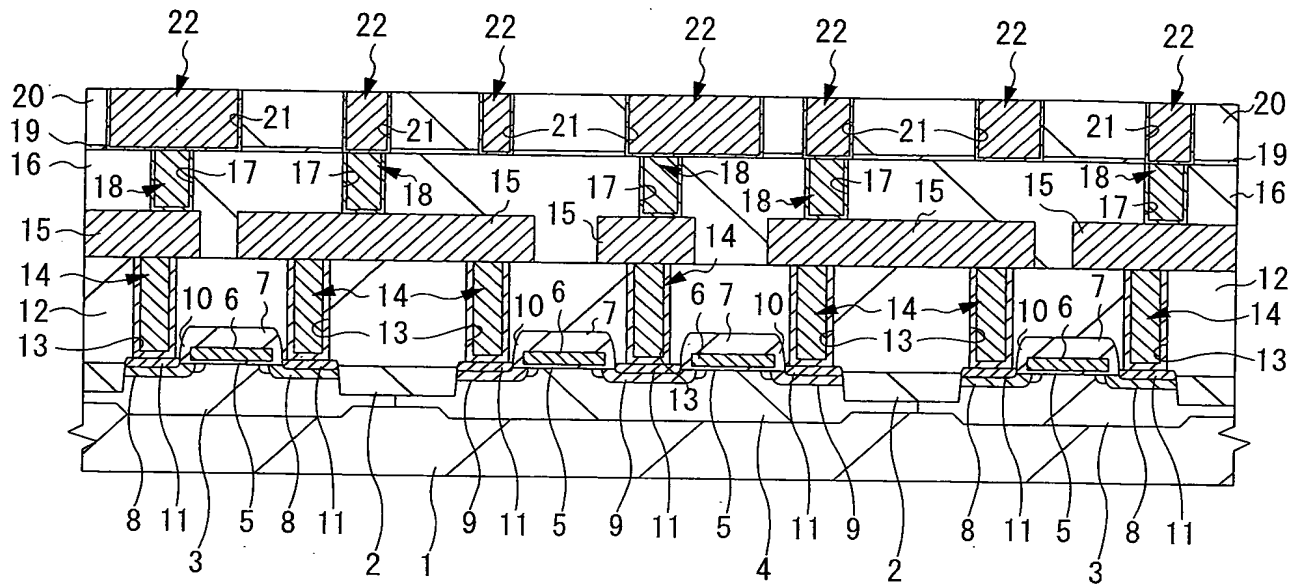


FIG. 9

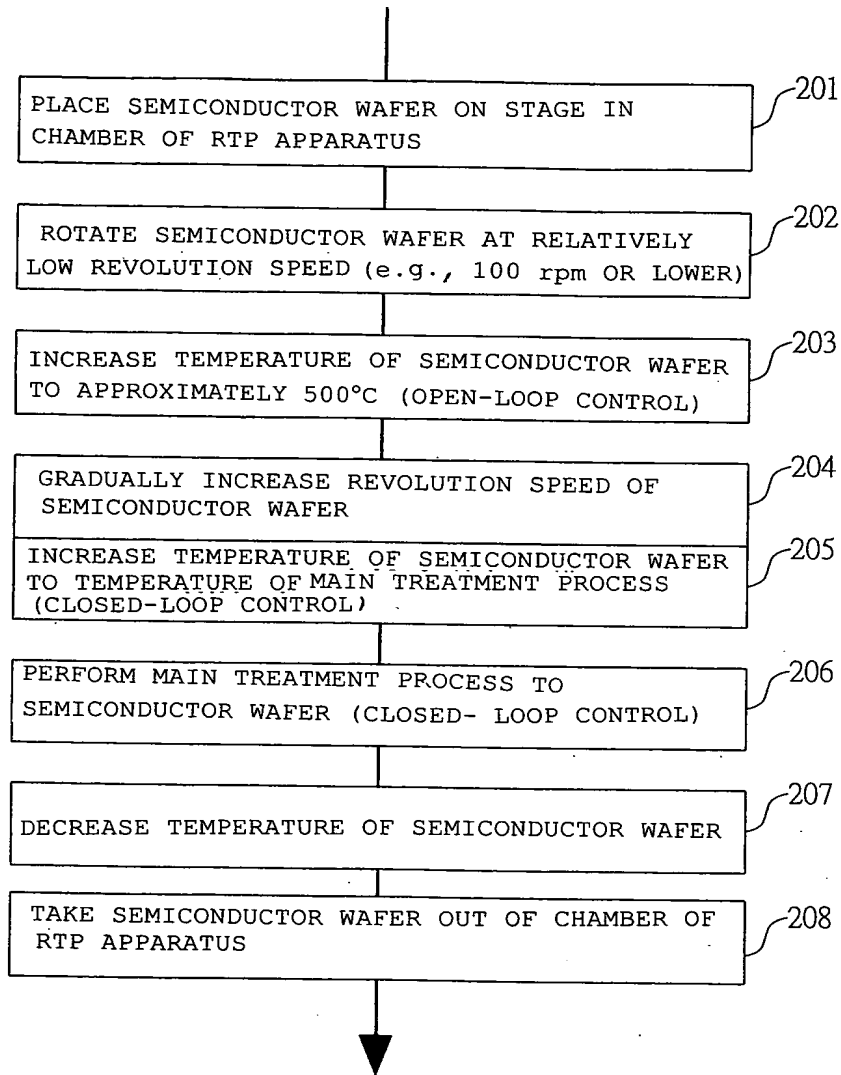


FIG. 10

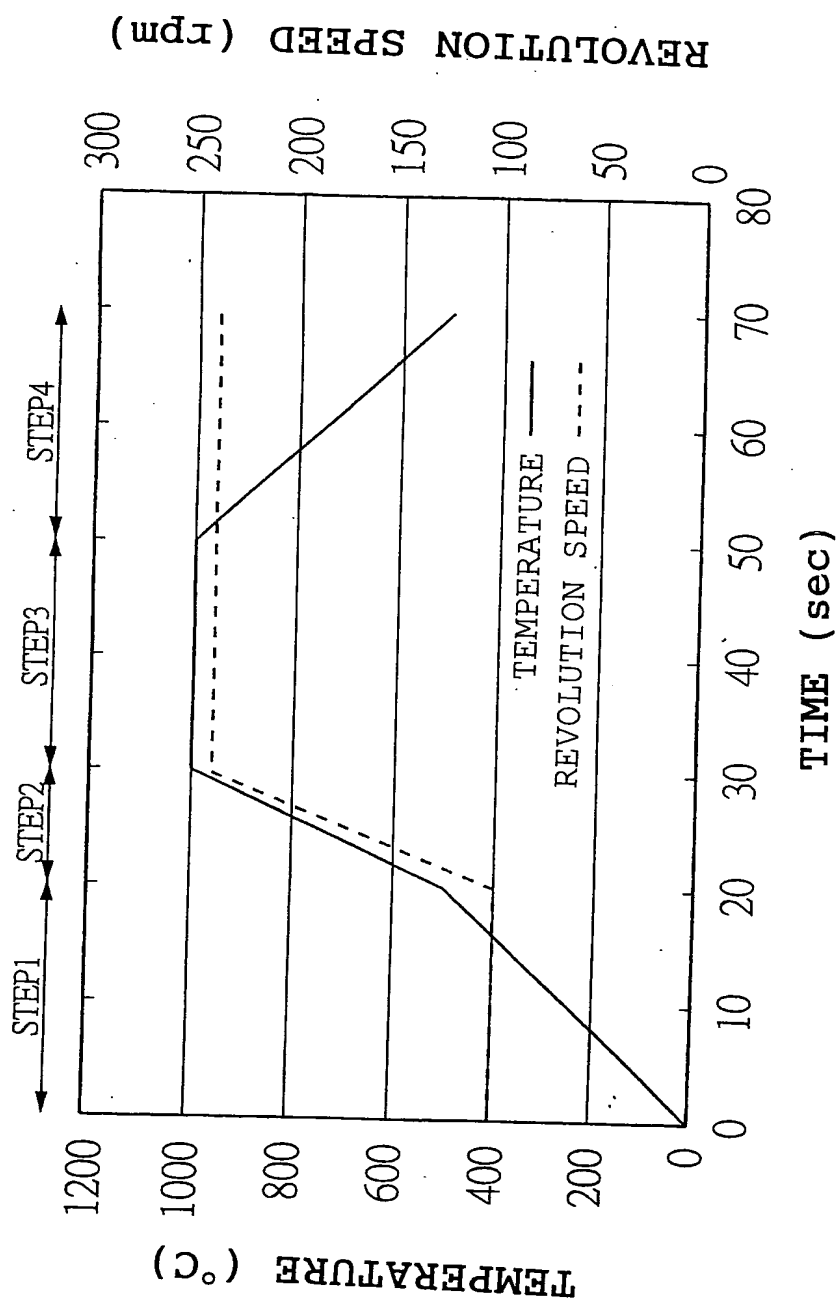


FIG. 11

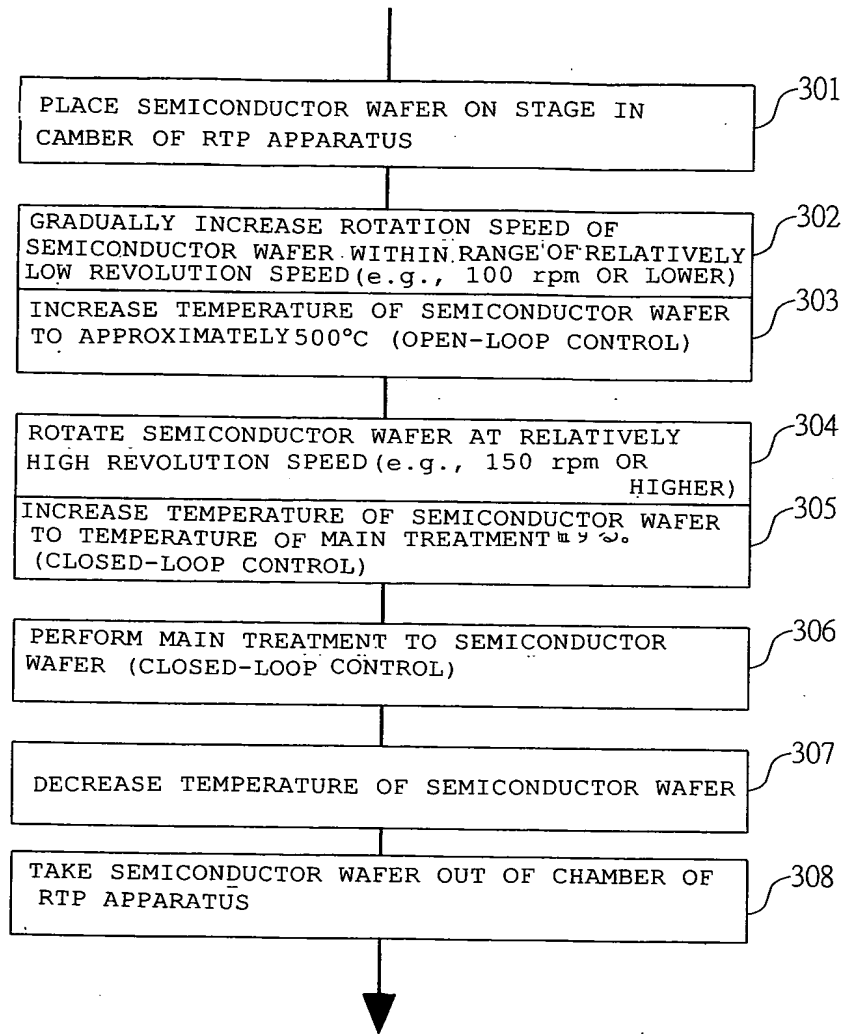


FIG. 12

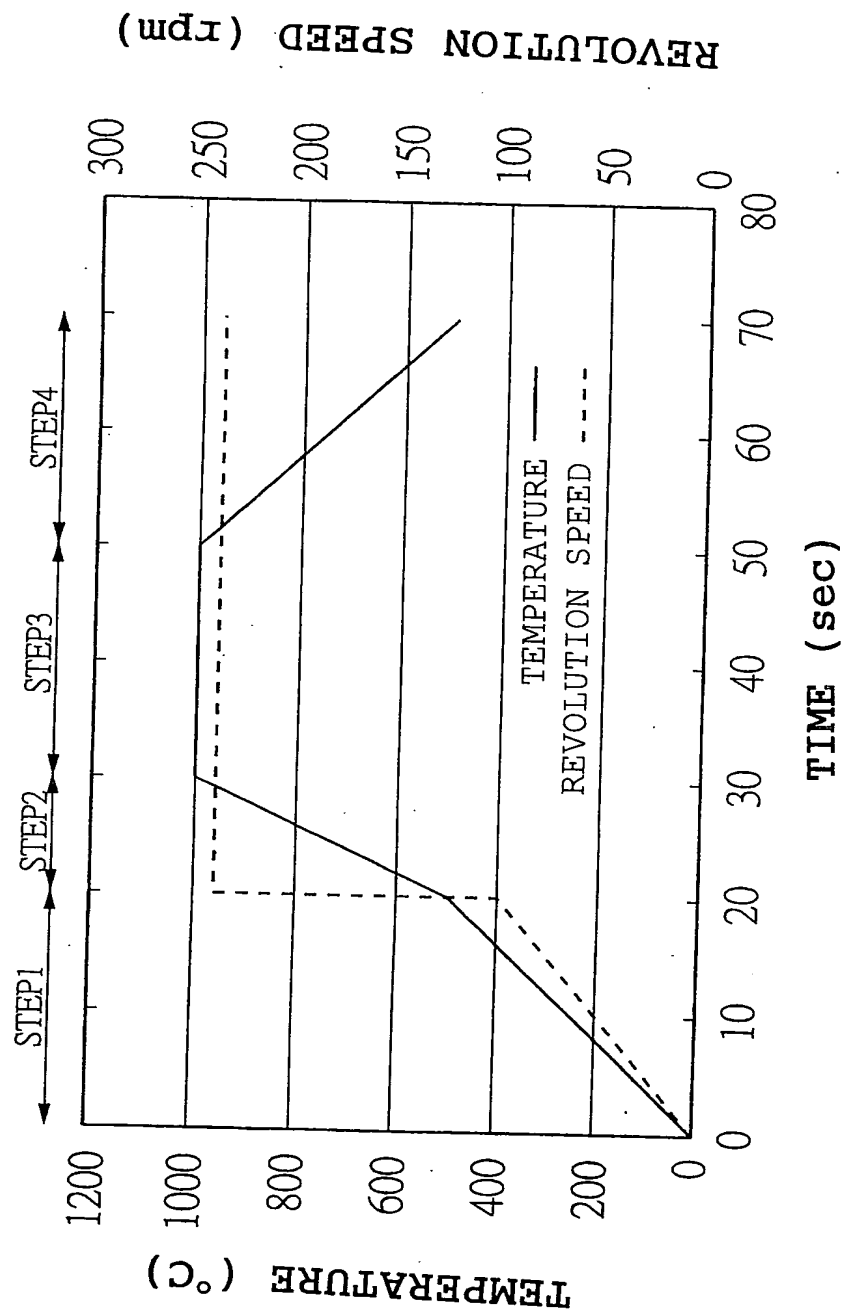


FIG. 13

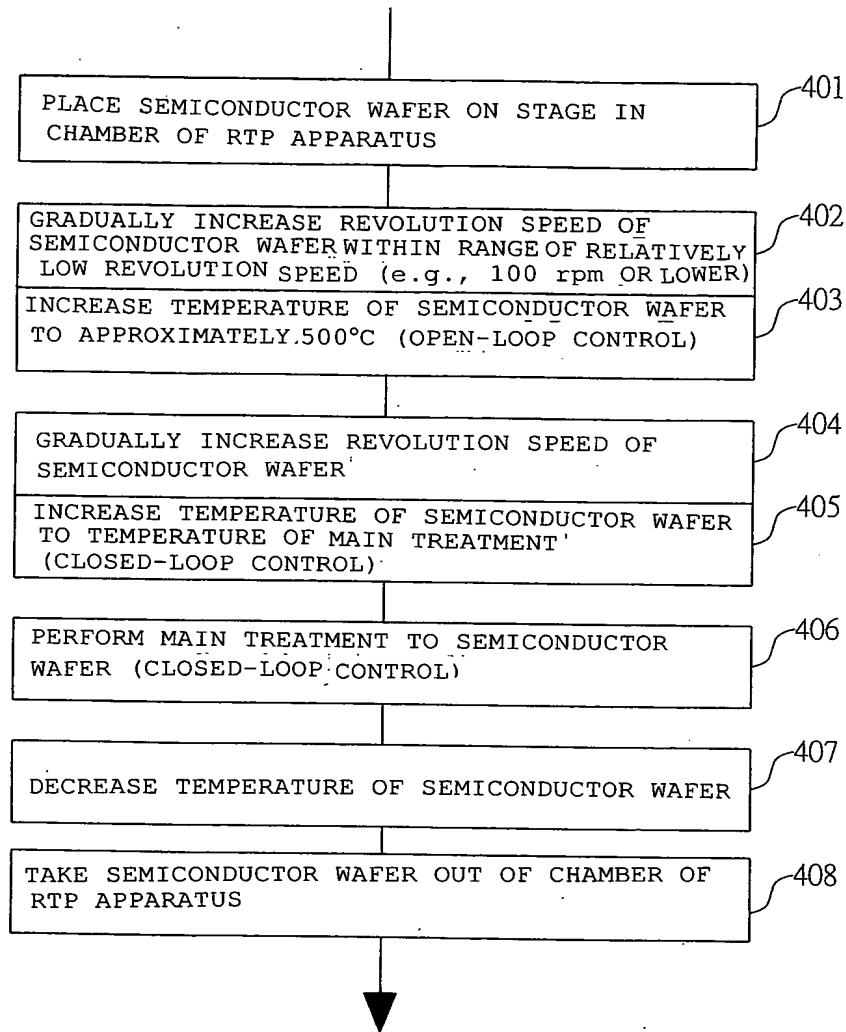


FIG. 14

